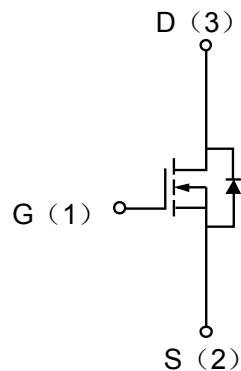


## Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
45	100@ $V_{GS}=10V$	2
	110@ $V_{GS}=4.5V$	
	160@ $V_{GS}=2.5V$	



## Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		$V_{DS}$	45	V
Gate-Source Voltage		$V_{GS}$	$\pm 12$	V
Drain Current	Continuous	$I_D$	2.0	A
	Pulsed	$I_D$	8	A
Source current(Body diode)	Continuous	$I_S$	0.8	A
	Pulsed	$I_{SP}$	8	A
Total Power Dissipation		$P_D$	1.0	W
Channel temperature		$T_{ch}$	150	°C
Range of storage temperature		$T_{stg}$	-55 to +150	°C

## Thermal resistance

Parameter	Symbol	Limits	Units
Channel to ambient	$R_{th(ch-a)}^*$	125	°C/W

## Body diode characteristics(Source-drain)(Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Units	Conditions
Forward voltage	$V_{SD}$	--	--	1.2	V	$I_S=0.8A, V_{GS}=0V$

## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	45		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 45\text{V}, V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = 12\text{V}$	-	-	1	$\mu\text{A}$
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	0.5		1.5	V
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	$V_{GS} = 10\text{V}, I_D = 2.0\text{A}$	-	100	130	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 2.0\text{A}$	-	110	150	$\text{m}\Omega$
		$V_{GS} = 2.5\text{V}, I_D = 2.0\text{A}$	-	160	220	$\text{m}\Omega$
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{V}, V_{DS} = 10\text{V}, f = 1\text{MHz}$	-	240		$\text{pF}$
Output Capacitance	$C_{DSS}$		-	30		$\text{pF}$
Reverse Transfer Capacitance	$C_{RSS}$		-	20		$\text{pF}$
<b>SWITCHING PARAMETERS</b>						
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DS} = 25\text{V}, V_{GS} = 4.5\text{V}, R_L = 25\Omega, R_G = 10\Omega, I_D = 1.0\text{A}$	-	6	--	ns
Rise time	$t_r$		--	15	--	ns
Turn-Off Delay Time	$t_{d(\text{off})}$		-	15	--	ns
Fall time	$t_f$		--	10	--	ns
Total gate charge	$Q_g$	$V_{DS} = 25\text{V}, V_{GS} = 4.5\text{V}, R_L = 12.5\Omega, R_G = 10\Omega, I_D = 2.0\text{A}$	--	2.9	4.1	nC
Gate-source charge	$Q_{gs}$		--	0.7	--	nC
Gate-drain charge	$Q_{gd}$		--	0.9	--	nC

## Typical Characteristics

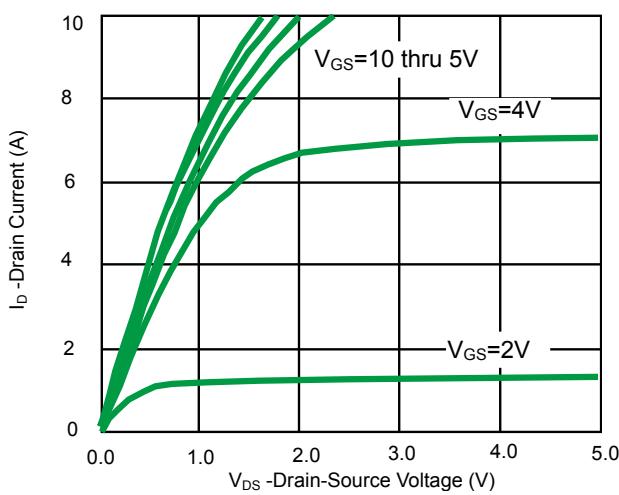


Fig 1. Output characteristics

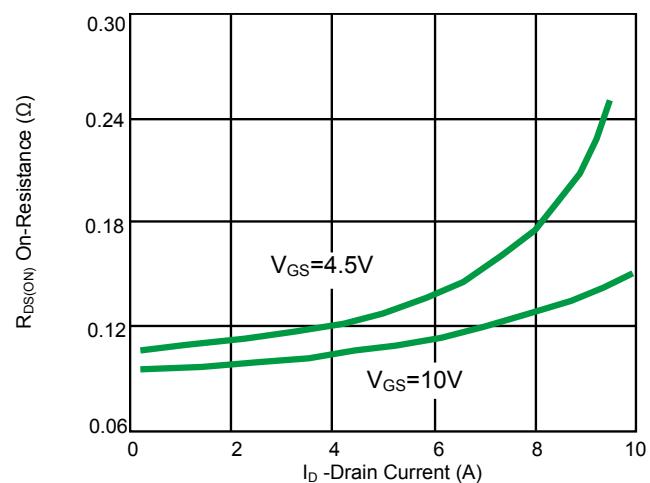


Fig 2. Drain-Source On-Resistance

## 2.5V Drive N-Channel MOSFET

PNMT45V2

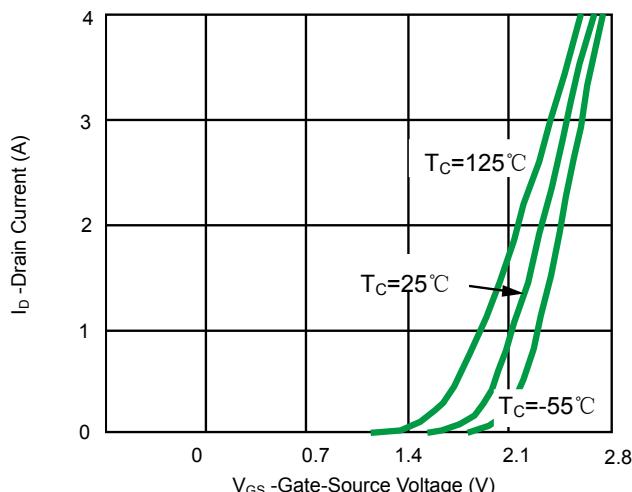


Fig 3. Transfer Characteristics

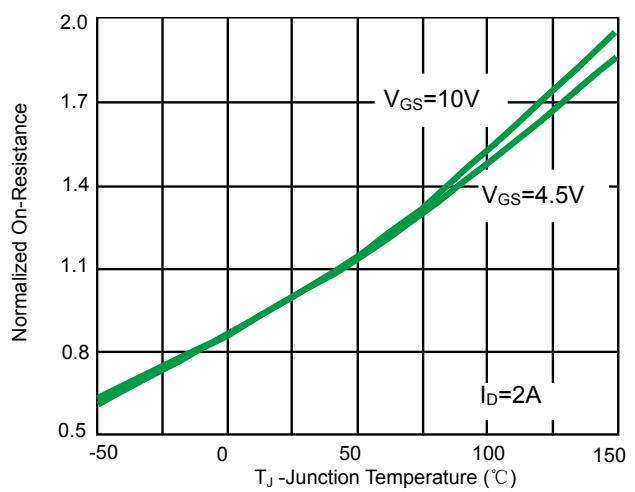


Fig 4. Drain-Source On-Resistance

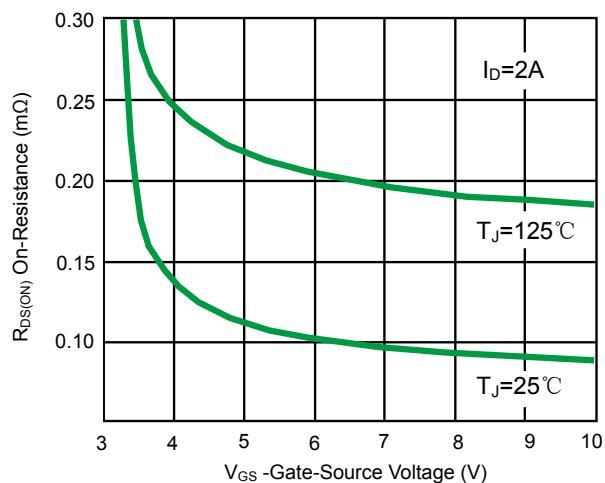


Fig 5.  $R_{DS(ON)}$  vs.  $V_{GS}$

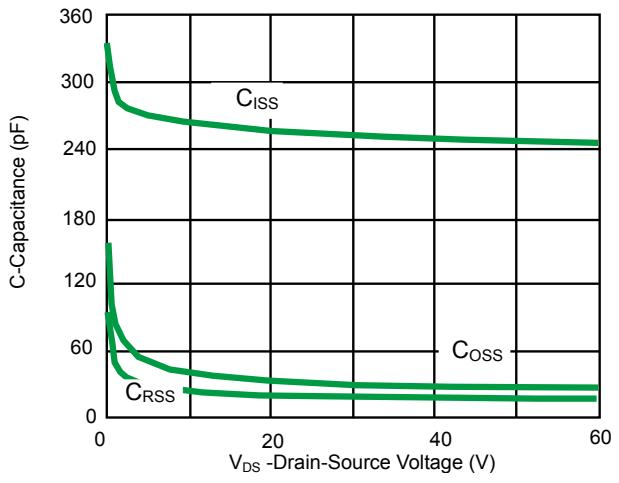


Fig 6. Capacitance vs.  $V_{DS}$

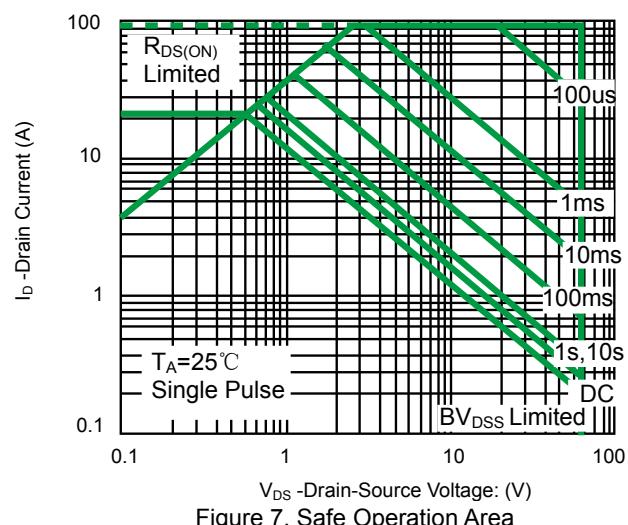


Figure 7. Safe Operation Area

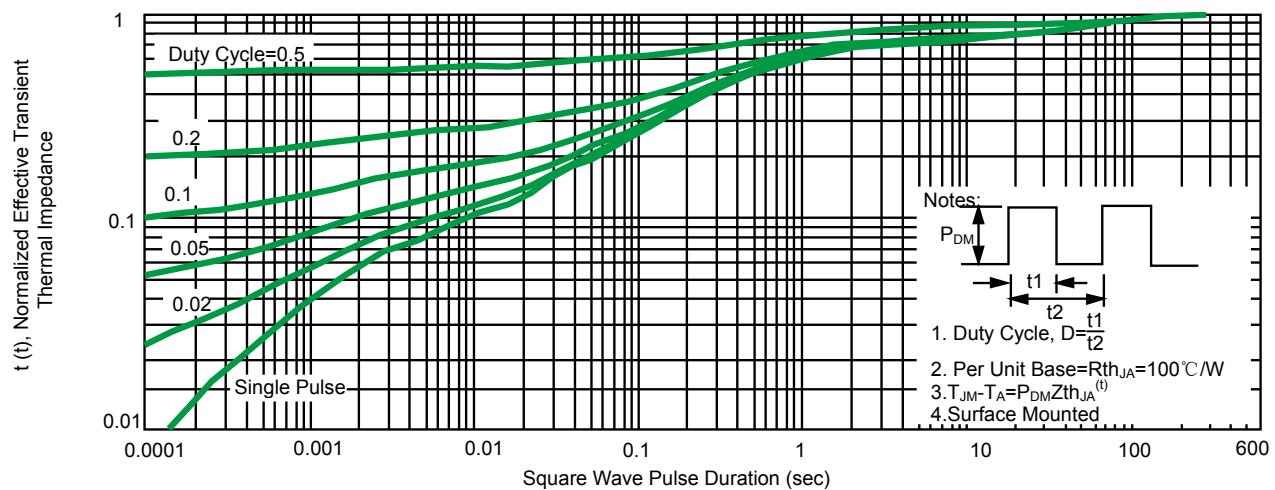
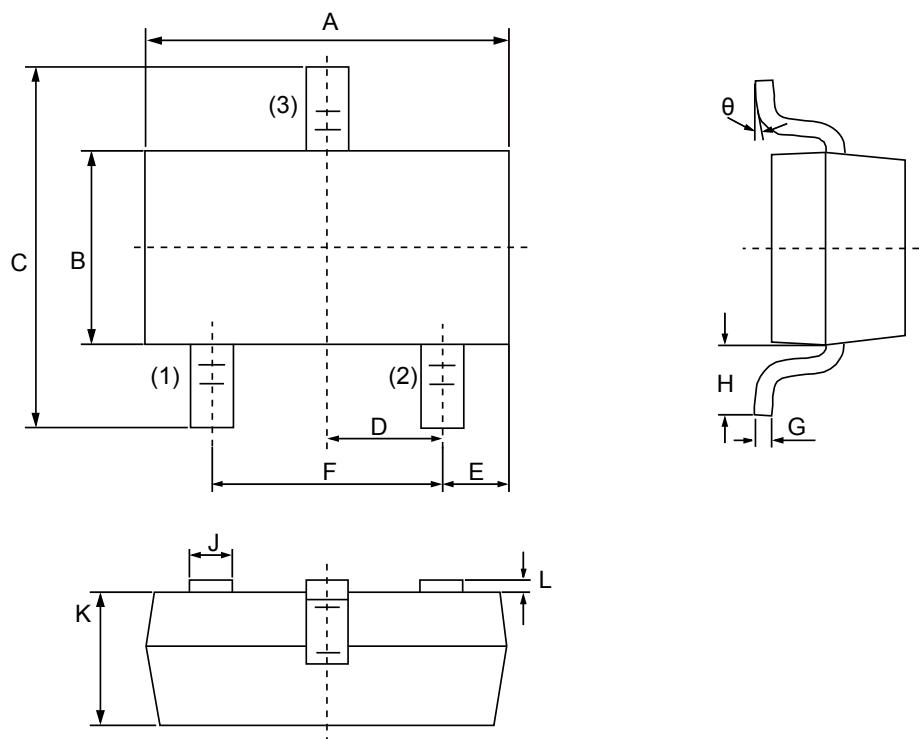
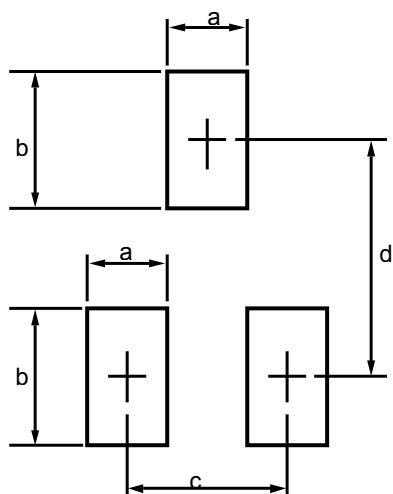


Fig 8.Normalized Maximum Transient Thermal Impedance

## Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.04	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°



Dim	Millimeters	
	MIN	MAX
a	--	0.7
b	--	1.2
c	--	2.04
d	--	2.2

## Ordering information

Device	Package	Shipping
PNMT45V2	SOT-23 (Pb-Free)	3000 / Tape & Reel

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